Joint International Conference on
The 8th ICMAP & The 9th ISFM

January 17-20, 2021 l Online Conference

[WC1] Plasma Deposition and Etching - III (ALE, PI-VM and MD Simulation)	
Date / Time	January 20 (Wed.), 2021 / 09:00-10:40
Place	Channel C
Session Chair(s)	Yeon Ho Im (Jeonbuk Nat'l Univ., Korea)

[WC1-1] **09:00-09:20**

Characteristics of Silicon Nitride Deposited by Very High Frequency (162 MHz)-Plasma Enhanced Atomic Layer Deposition Using Bis(diethylamino)silane

Youjin Ji[1], Kihyun Kim[1], Jieun Kang[1], Youngsim Kim[1], Albert Rogers Ellingboe[2], and Geunyoung Yeom[1]

[1]Sungkyunkwan Univ., Korea, [2]Dublin City Univ., Ireland

[WC1-2] **09:20-09:40**

Construction of Classical Interatomic Potential Functions for Molecular Dynamics Simulation of Si and SiO_2 Etching by I^+ Ions

Erin Joy Capdos Tinacba, Michiro Isobe, and Satoshi Hamaguchi

Osaka Univ., Japan

[WC1-3] **09:40-10:00**

Development of Virtual Metrology Using Plasma Information (PI-VM) on $Ge_xSb_yTe_z$ Pattern Etch for PRAM

Jaemin Song, Myeong-Geon Lee, Yunchang Jang, Chanyoung Yoo, Cheol Seong Hwang, and Gon-Ho Kim

Seoul Nat'l Univ., Korea

[WC1-4] **10:00-10:20**

Study of SiO_2 Etching Using $C_xH_2F_6$ (x=3,4) L-HFC Precursors

Hyun Woo Tak, Da In Sung, In Pyo Hong, Wen Long, Dong Woo Kim, and Geun Yong Yeom

Sungkyunkwan Univ., Korea

[WC1-5] **10:20-10:40**

A Study on the Atomic Layer Etching Using Radio-frequency biased Inductively Coupled Plasma in Ar/C_4F_6 Mixture

Min Young Yoon[1], Jung Hyung Kim[1], Jong-Ryul Jeong[2], and Hyo-Chang Lee[1]

[1]KRISS, Korea, [2]Chungnam Nat'l Univ., Korea